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(54) Abstract Title

**Spin-on glass composition and method of forming silicon oxide layer**

(57) A silicon oxide layer is formed by coating on a semiconductor substrate having a surface discontinuity, an SOG composition containing perhydropolysilazane having a compound of the formula  $-(SiH_2NH)_n-$  wherein  $n$  represents a positive integer, a weight average molecular weight within the range of about 4,000 to 8,000, and a molecular weight dispersion within the range of about 3.0 to 4.0, to form a planar SOG layer. The SOG layer is converted to a silicon oxide layer with a planar surface by curing the SOG layer. Solvent is present in the composition in an amount of 70-90% by weight.

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